

PROPOSED CLAIM CHANGES

11. (Amended) [Device] A protection device for protection of an electronic component against electrostatic discharges, [the device being made] comprising:

a plurality of Zener diodes formed in a semiconducting layer of a semiconducting substrate, the semiconducting layer covering an insulating layer[,] and having two regions of heavy doped opposite conductivity types extending across the semiconductor layer; and ^{at depth} _{(Col. 22, 40-45) & Col. 23, lines 1-10}
[the device being connected to] a contact pin connected to the electronic component and connected through the Zener diodes to ground [to protect the component] in order to divert an electrostatic discharge and thereby protect the electronic component, the device comprising at least one Zener diode connected to the contact pin to be directly polarized].

Fig. 19/10 (Zener) Fig. 16 I (28 → Ø V)
12. (Amended) Device according to claim 11, [further comprising] wherein said plurality of Zener diodes are mounted in series and connected to the contact pin [to be directly polarized].

13. (Amended) Device according to claim 11, wherein the [at least one Zener diode comprises] two regions are strongly doped with said opposite conductivity types, the two regions being separated by a region doped to an average level according to either of the opposite conductivity types.

14. (Amended) Device according to claim 13, wherein the semiconducting layer [of the substrate is] comprises a silicon layer, the [doping of the two regions with] ~~strong doping~~ ^{heavily doped} ~~region~~ [being] is of the order of 10^{20} atoms/cm³, the [doping of the] region doped to an average [with medium] level [doping being] is of the order of 10^{18} atoms/cm³. *Col. 24, lines 40-50*

15. (Amended) Device according to claim 11, wherein the [said] semiconductor substrate is [an] a silicon-on-insulator SOI substrate.

16. (Amended) Device according to claim 12, wherein the plurality of the Zener diodes is [are] laid out adjacent to each other to form a series installation, and an electrical link between two adjacent Zener diodes [being] is obtained by a metallization.

17. (Amended) Device according to claim 12, wherein the plurality of the Zener diodes are laid out adjacent to each other to form a series installation, and an electrical link between two adjacent Zener diodes [being] is obtained by a silicide.

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Dear Examiner Schillinger:

Below are proposed changes to this case submitted here in advance of the interview scheduled for Monday, November 4, 2002 at 12:00 Noon. The proposed changes address the claim objection raised in the outstanding Office Action, and amends Claim 11 to define that the Zener diode includes two regions of heavy doped opposite conductivity types extending across the semiconductor layer. Such regions extending throughout the semiconductor layer containing the Zener diode is not taught in the applied prior art.

Best regards,

Ron Rudder

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